XF-R 3-1
磁场探头（30MHz-6GHz）

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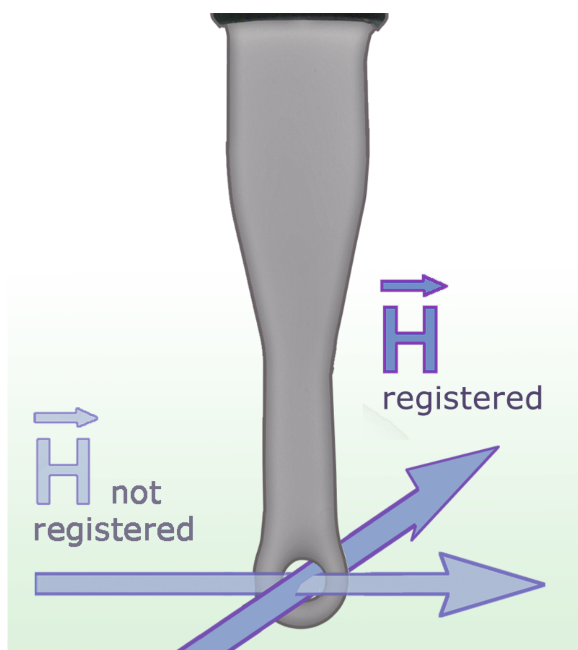


Short description

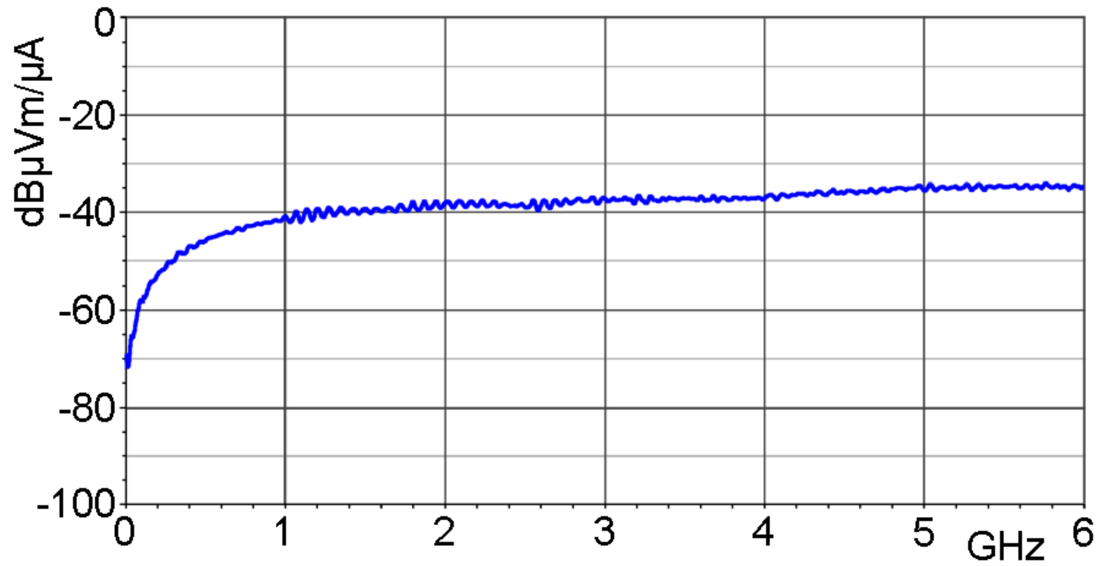
XF-R 3-1型近场探头： 用于高分辨率直接检测组件上，譬如IC的引脚或外壳、布线、旁路电容器和电磁兼容性（EMC）元件等区域的射频磁场。

In principle the XF-R 3-1 H-field probe has the same structure as the XF-R 100-1 and XF-R 400-1 probes. The resolution of the XF-R 3-1 is significantly higher. The H-field probe is suitable for measurements close to the components with high magnetic field strength. It is not suitable for measurements from large distances, which can be done using XF-R 400-1 and XF-R 100-1. The near-field probe is small and handy. It has a current attenuating sheath and, therefore, is electrically shielded. It can be connected to a spectrum analyzer or an oscilloscope with a 50 Ω input. The H-field probe has an internal terminating resistance.

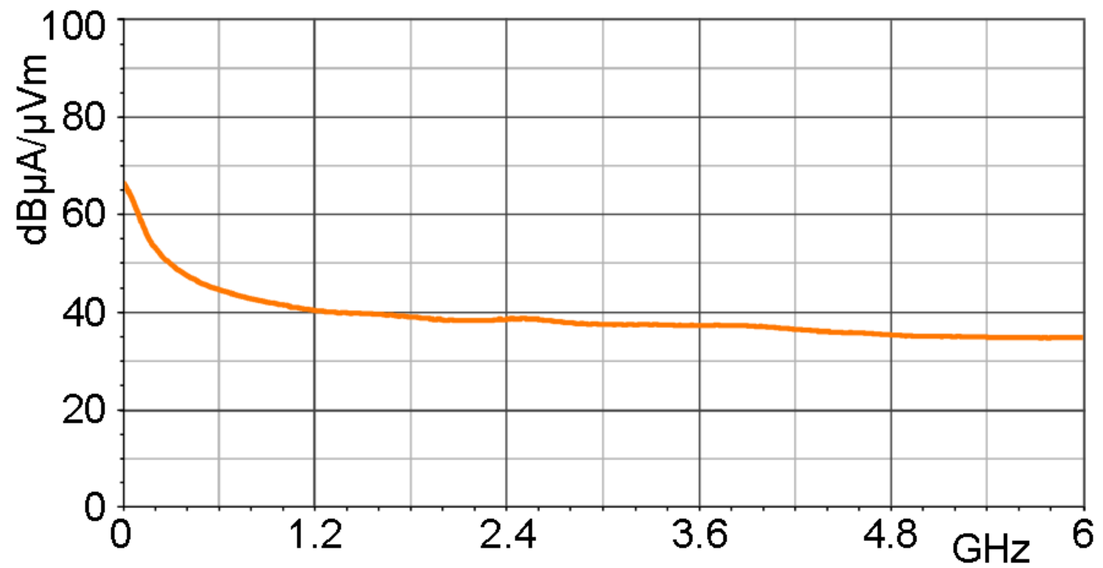
Technical parameters

频率范围	30 MHz ... 6 GHz
分辨率	≈ 1 mm
探头尺寸	Ø ≈ 3 mm
输出接口	SMA, female, jack
重量	15 g

频率特性 [dBµV] / [dBµA/m]



磁场校正曲线 [dBµA/m] / [dBµV]



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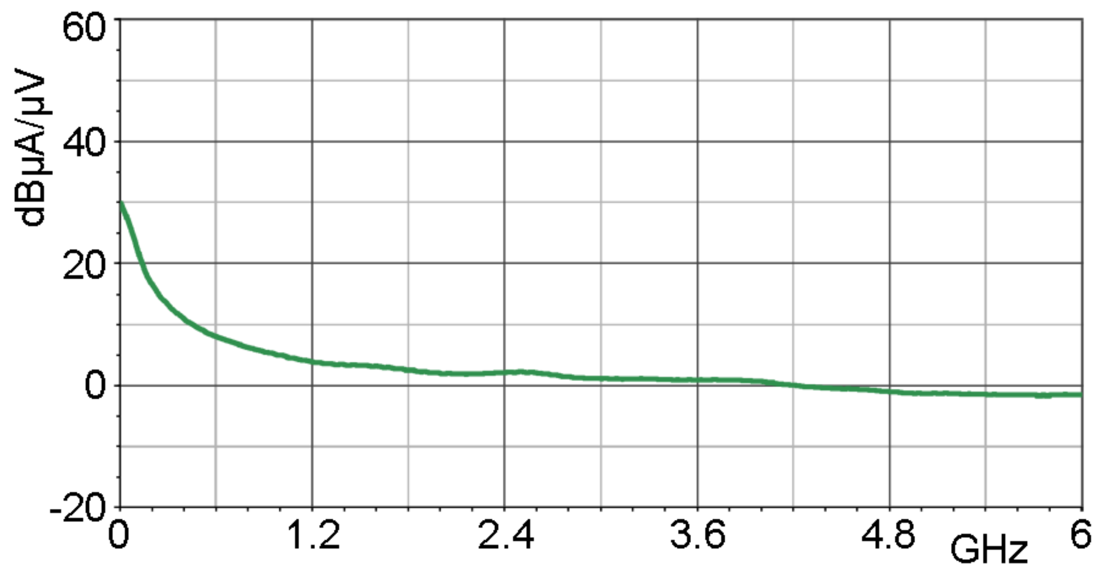
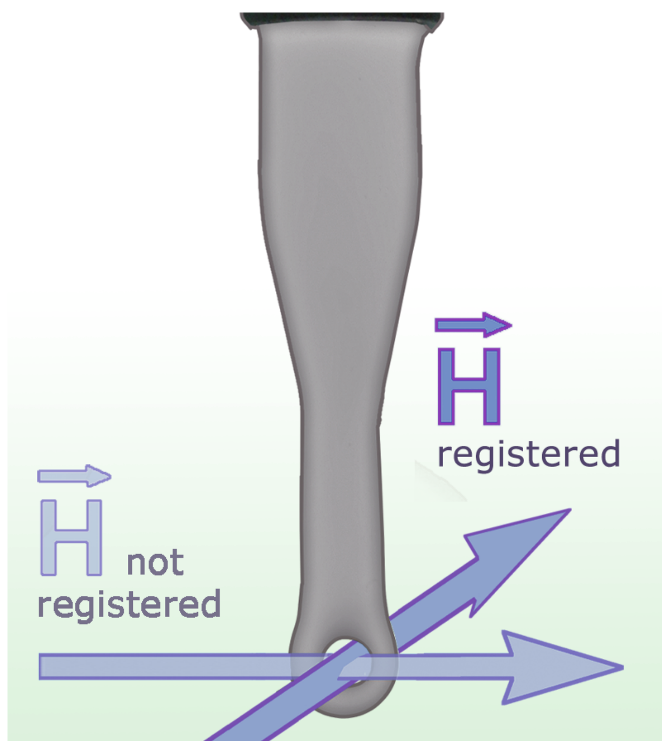
电流校正曲线 [dBµA] / [dBµV]





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Probe head